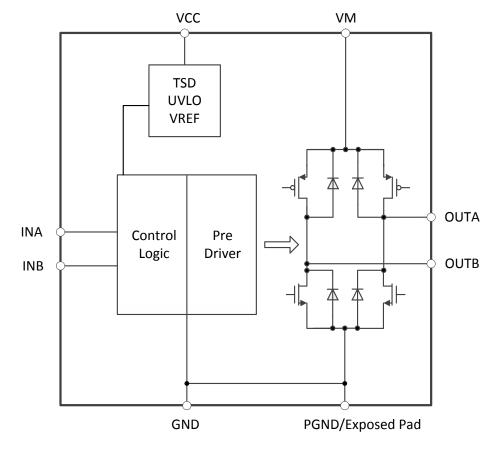# DESCRIPTION

The BDR6133 is 1 Full-On Drive H-Bridge channel with two different packages. The driver features wide range operating from 2V to 24Vand low power consumption by fast switching speed.

APPLICATIONS

- DC brushed motor
- Auto icemaker or dumper drive for refrigerator
- Intelligent electronic lock

FEATURES

- It is low consumption by BCD process adoption
- Small packages: ESOP8
- Wide power-supply voltage range:
    -Control (VCC): 2.7V~5.5V
    - Motor (VM): 2.0V~24V
- High DC output current: Max.=2.8A
- Ultra low RDSON(TOP+BOT):
  0.51ΩTYP@25°C, 1A for ESOP8;
- Low current consumption when power-down: <0.05μA @25°C
- PWM control, Max. input frequency: 200KHz.
- Operating temperature range: -40~+85°C
- Charge-pump less
- Shoot-through current protection
- Built-in protection circuits
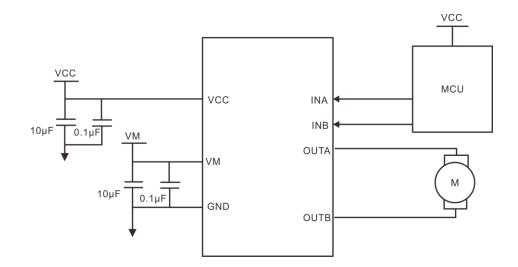   - Under voltage lock out
- - Thermal shut down

BLOCK DIAGRAM

Note: GND and PGND/Exposed Pad are connected together internally.
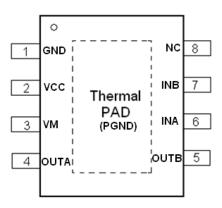
APPLICATION CIRCUITS

ESOP8

ORDER INFORMATION

Valid Part Number	Package Type	Top Code
BDR6133	8pins,ESOP	BDR6133

PIN CONFIGURATION

ESOP8

PIN DESCRIPTION

Pin Name	I/O	Description	Pin No.
NC	-	NC pin	8
GND	GND	Ground	1
VCC	Power	Power supply for logic circuit	2
VM	Power	Power supply for driver	3
OUTA	O	H-Bridge output terminal A of the driver	4
OUTB	O	H-Bridge output terminal B of the driver	5
INA	I	Control input	6
INB	I	Control input	7
PGND	GND	Power MOS GND	Thermal PAD

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SHEN ZHEN BARDEEN MICROELECTRONICS CO.,LTD

FUNCTION TABLE

INPUT-OUTPUT LOGIC TABLE

Input Signal		Output Driver		Actuator status
INA	INB	OUTA	OUTB	
L	L	Z	Z	Stand-by(Stop)
L	H	L	H	Reverse
H	L	H	L	Forward
H	H	L	L	Brake

FUNCTION SEQUENCE

Note: VM & VCC power on have no timing sequence

VM & VCC power off have no timing sequence

PROTECTION FUNCTION

THERMAL SHUTDOWN (TSD) CIRCUIT

The BDR6133 includes a thermal shutdown circuit, which turns the output transistors off when the junction temperature (Tj) exceeds 175°C (typ.).

The output transistors are automatically turned on when Tj cools past the shutdown threshold, which is lowered by a hysteresis of 30°C.

TSD = 175°C
ΔTSD = 30°C

* In thermal shutdown mode, the circuits powered by VCC are work normal, and the circuits powered by VM are shut down.

UNDER VOLTAGE LOCKOUT (UVLO) CIRCUIT

The BDR6133 includes an under voltage lockout circuit, which puts the output transistors in the high-impedance state when VCC decreases to 2.13V (typ.) or lower.
The output transistors are automatically turned on when VCC increases past the lockout threshold, which is raised to 2.21 V by a hysteresis of 0.08 V.

*In UVLO shutdown mode, a part of circuits powered by VCC are work normal, and the circuits powered by VM are shut down.

SHOOT-THROUGH CURRENT PROTECTION

During Dead Time (Shoot through current circuit is operated.), Power MOS both of HI side and Low side are turned off. But in this time, internal parasitic diode is turned on according to current direction.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit	Note
Supply voltage VCC	VCC	-0.5	6	V	
Control input voltage	INA/INB	-0.5	6	V	
Supply voltage VM	VM	-0.5	26	V	
H-Bridge output current DC	Iload_dc_MD	-	2.8	A	
H-Bridge output current AC	Iload_peak_MD	- -	4.8 7.5	A A	Note1 Note2
Continuous power dissipation	Pd Ta=25℃	-	3	W	Note4
	Pd Ta=85℃	-	1.6	W	
Operation temperature	Ta	-40	85	℃	
Junction temperature	Tj	-	150	℃	
Storage temperature	Tstg	-40	150	℃	
Minimum ESD rating(HBM)	Vesd	2000	-	V	
Minimum ESD rating(MM)	Vesd	200	-	V	

Notes:

1. Terminal OUTA,OUTB pulse with =<200ms:Duty 5%

2. Terminal OUTA,OUTB pulse with =<200ms:Duty 1%

3.   Maximum power dissipation is a function of TJ(max), Rja, and TA. The maximum allowable power dissipation at any allowable ambient temperature is PD = (TJ(max) − TA)/Rja. Operating at the absolute maximum TJ of 150°C can affect reliability.

4. The package thermal impedance for ESOP8 is calculated in accordance with JEDEC, 2S2P test PCB, Rja=41℃/W

RECOMMENDED OPERATION CONDITIONS

Parameter	Symbol	Min	Typ.	Max	Unit
Supply voltage VCC	VCC	2.7	3.3	5.5	V
Control input voltage	INA/INB	1.62	1.8/3.3	VCC	V
Supply voltage VM	VM	2	-	24	V
Logic input frequency	Fin	0	-	200	KHz
Logic input duty for frequency=200KHz (Ta=25℃, VCC=3.3V,VM=12V, Rload=50Ω, Output state: Forward↔Reverse)	Duty	6%	-	94%	%

ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, Ta=25℃, VCC=3.3V, VM=7.4V)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
VDET1						
VCC UVLO	VCDET_LV		1.90	2.13	2.50	V
TSD (Note)						
Thermal shut down temperature	TDET		-	175	-	℃
Hysteresis	TDETHYS		-	30	-	℃
Power Supply Current						
VM standby current1	IVM_NOPOW	VCC=L	-	0.005	0.05	µA
VM standby current2	IVM_STBY	INA=INB=L	-	0.005	0.05	µA
VCC work current	IVCC_ WORK	INA=H, INB=L	-	130	300	µA
Operation circuit current	IVCC_PWM	INA=200KHz,INB=H	-	0.38	0.8	mA
Driver						
Output onresistance 1 (HSD or LSD)	RON1	VCC=3.3V,IOUT=100mA Ta=25℃	-	0.25	0.27	Ω
Output onresistance 2 (HSD or LSD)	RON2	VCC=3.3V,I$_{OUT}$=1.0A Ta=25℃(Tj=65℃)	-	0.255	0.29	Ω
Output onresistance 3 (HSD or LSD)	RON3	VCC=3.3V,I$_{OUT}$=1.0A Ta=85℃(Tj=125℃)	-	0.295	0.35	Ω
Diode forward voltage	VF_MD	IF=100mA	-	0.7	1.2	V
Control Terminal						
H level input voltage(INA, INB)	VIH		0.7xVCC	-	-	V
L level input voltage(INA, INB)	VIL		-	-	0.3xVCC	V
H level input current(INA, INB)	IIH1		-	-	1	µA
L level input current(INA, INB)	IIL1		-	-	1	µA
Full Swing						
Turn on time 1	TfONH	VCC=3.3V,VM=7.4V I$_{OUT}$=500mA, Output state: Forward→Reverse. Refer to Fig.1	-	0.42	1.0	µs
Turn off time 1	TfOFFH		-	0.11	0.5	µs
Output rise time 1	Tfr		-	0.09	1.0	µs
Output fall time 1	Tff		-	0.04	0.5	µs
Turn on time 2	TrONH	VCC=3.3V,VM=7.4V I$_{OUT}$=500mA, Output state: Reverse→Forward. Refer to Fig.1	-	0.38	1.0	µs
Turn off time 2	TrOFFH		-	0.11	0.5	µs
Output rise time 2	Trr		-	0.09	1.0	µs
Output fall time 2	Trf		-	0.04	0.5	µs
Turn on time 1	TfONH	VCC=3.3V,VM=7.4V I$_{OUT}$=500mA, Output state: STBY→Forward/Reverse. Refer to Fig.2	-	2.10	10	µs
Output rise time 1	Tfr		-	0.09	1.0	µs
Turn off time 1	TfOFFH	VCC=3.3V,VM=7.4V I$_{OUT}$=500mA, Output state: Forward/Reverse→STBY Refer to Fig.2	-	0.11	0.5	µs
Output fall time 1	Tff		-	0.04	0.5	µs

Note: OUTA and OUTB are Hi-Z (off state) at thermal shut down.

SWITCHING CHARACTERISTICS WAVEFORM
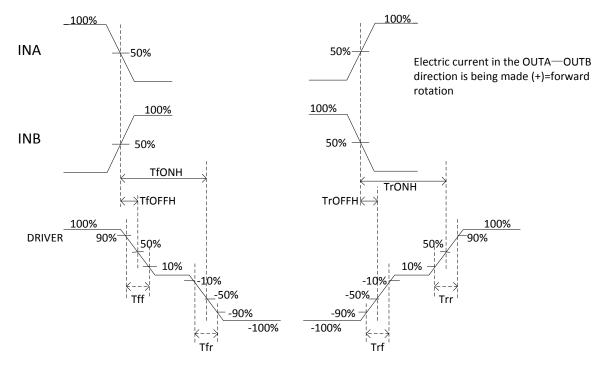
SWITCHING WAVEFORM
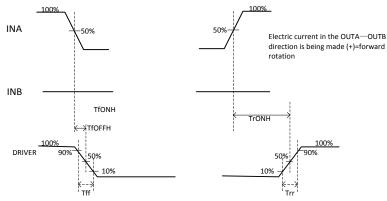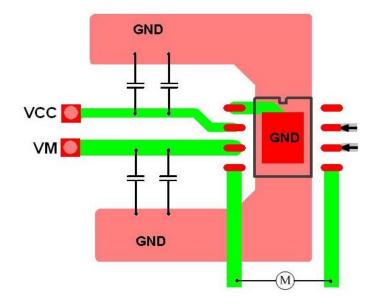
Fig.1 switching characteristics waveform
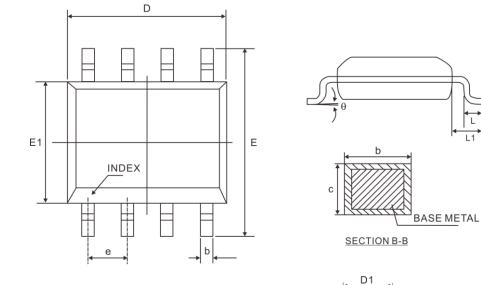
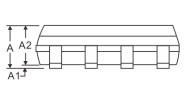Fig.2 switching characteristics waveform

PCBLAYOUT

8-PIN, ESOP

PACKAGE INFORMATION

8-PIN, ESOP

Symbol	Dimensions(mm)		
	Min.	Nom.	Max.
A	-	-	1.70
A1	0.00	-	0.15
A2	1.25	-	-
b	0.31	-	0.51
c	0.17	-	0.25
e	1.27 BSC		
D	4.90 BSC		
D1	3.1	3.3	3.5
E	6.00 BSC		
E1	3.90 BSC		
E2	2.2	2.4	2.6
L	0.40	-	1.27
L1	1.04 REF		
θ	0°	-	8°

Notes:

1. Refer to JEDEC MS-012 BA

2. All dimensions are in millimeter.

3. D1 and E2 refer to supplier spec. The JEDEC MS-012BA classify D1 and E2 minimum value are 1.5mm and 1.0mm.

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